

ETR0202_001

Voltage Detectors, Delay Circuit Built-In

■GENERAL DESCRIPTION

The XC61F series are highly accurate, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies. A delay circuit is built-in to each detector.

Detect voltage is extremely accurate with minimal temperature drift.

Both CMOS and N-channel open drain output configurations are available.

Since the delay circuit is built-in, peripherals are unnecessary and high density mounting is possible.

■APPLICATIONS

- Microprocessor reset circuitry
- Memory battery back-up circuits
- ●Power-on reset circuits
- Power failure detection
- System battery life and charge voltage monitors
- Delay circuitry

■FEATURES

Highly Accurate : ± 2%

Low Power Consumption : $1.0 \mu A(TYP.)[VIN=2.0V]$

Detect Voltage Range : 1.6V ~ 6.0V in 100mV increments

Operating Voltage Range : 0.7V ~ 10.0V Detect Voltage Temperature Characteristics

:±100ppm/°C(TYP.)

Built-In Delay Circuit : 1 1ms ~ 50ms

② 50ms ~ 200ms

③ 80ms ~ 400ms

Output Configuration

CMOS

Mini Mold Package

Ultra Small Packages : SOT-23 (150mW) mini-mold

: SOT-89 (500mW) mini-power mold

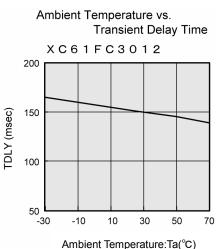
: N-channel open drain or CMOS

: TO-92 (300mW)

■TYPICAL APPLICATION CIRCUITS

$V_{\rm IN}$ $V_{\rm IN}$ $V_{\rm IN}$ $V_{\rm IN}$ $V_{\rm IN}$ $V_{\rm IN}$ $V_{\rm OUT}$ $V_{\rm OUT}$ $V_{\rm SS}$ $V_{\rm SS$

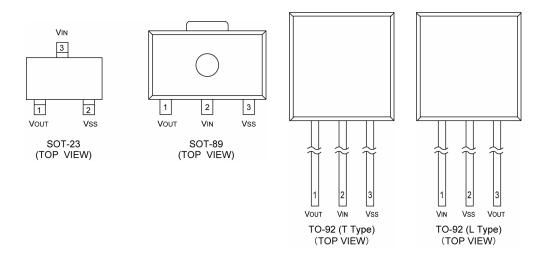
■TYPICAL PERFORMANCE CHARACTERISTICS



Ambient Temperature. Ta(C

^{*} No parts are available with an accuracy of ± 1%

■PIN CONFIGURATION



■PIN ASSIGNMENT

PIN NUMBER			PIN NAME	FUNCTION	
SOT-23	SOT-89	TO-92 (T)	TO-92 (L)	FIIN INAIVIE	FUNCTION
3	2	2	1	Vin	Supply Voltage Input
2	3	3	2	Vss	Ground
1	1	1	3	Vout	Output

■PRODUCT CLASSIFICATION

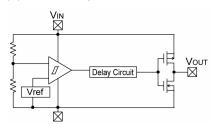
Ordering Information

XC61F (1)(2)(3)(4)(5)(6)(7)

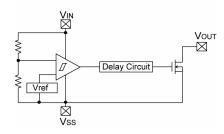
<u> </u>				
DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION	
1	Output Configuration	С	: CMOS output	
U	Output Configuration	N	: N-ch open drain output	
2 3	Detect Voltage	16 ~ 60	: e.g. 2.5V → ②2, ③5	
2 9	Detect Voltage	10 ** 00	: e.g. 3.8V → ②3, ③8	
		1	: 50ms ~ 200ms	
4	Output Delay	4	: 80ms ~ 400ms	
		5	: 1ms ~ 50ms	
(5)	Detect Accuracy	2	: Within ± 2.0%	
		М	: SOT-23	
6	Package	Р	: SOT-89	
0	Fackage	Т	: TO-92 (Standard)	
		L	: TO-92 (Custom pin configuration)	
	Device Orientation	R	: Embossed tape, standard feed	
7)		L	: Embossed tape, reverse feed	
		Н	: Paper type (TO-92)	
		В	: Bag (TO-92)	

■BLOCK DIAGRAMS

(1) CMOS output



(2) N-channel open drain output



■ABSOLUTE MAXIMUM RATINGS

Ta = 25°C

PARAMETER		SYMBOL	RATINGS	UNITS	
Input Voltage		VIN	12.0	V	
Output Current		lout	50	mA	
Output Voltage	CMOS	Vout	Vss -0.3 ~ Vin + 0.3	V	
Output voitage	N-ch open drain	V 001	Vss -0.3 ~ 9		
	SOT-23	Pd	150		
Power Dissipation	SOT-89		500	mW	
	TO-92		300		
Operating Temperature Range		Topr	-30~+85	°C	
Storage Temperature Range		Tstg	-40~+125	°C	

■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	CONDITION	S	MIN.	TYP.	MAX.	UNITS
Detect Voltage	VDF			VDF(T)	VDF(T)	VDF(T)	V
Detect voltage	V DF			x 0.98		x 1.02	V
Hysteresis Range	VHYS			VDF	VDF	VDF	V
Trysteresis Mange	VHIS			x 0.02	x 0.05	x 0.08	V
		_	VIN = 1.5V	-	0.9	2.6	
		_	VIN = 2.0V	-	1.0	3.0	
Supply Current	Iss		VIN = 3.0V	-	1.3	3.4	μ A
			VIN = 4.0V	-	1.6	3.8	
			VIN = 5.0V	-	2.0	4.2	
Operating Voltage	Vin	VDF= 1.6V to 6	6.0V	0.7	-	10.0	V
			VIN = 1.0V	-	2.2	-	
		N-ch VDF =0.5V	VIN = 2.0V	-	7.7	-	mA
	Іоит		VIN = 3.0V	-	10.1	-	
Output Current			VIN = 4.0V	-	11.5	-	
		-	VIN = 5.0V	-	13.0	-	
		CMOS, P-ch VDF=2.1V	VIN = 8.0V	-	-10.0	-	
Detect Voltage	ΔVDF						
Temperature	∆Topr∙			-	±100	-	ppm/°C
Characteristics	VDF						
Transient Delay Time	TDLY*	\(\(\text{\tint{\text{\tint{\text{\tin}\text{\ticl{\text{\tex{\tex		50		200	mo
(VDR → VOUT inversion)	IDLY	VIN changes from 0.6V to 10V		50	-	200	ms

VDF (T): Setting detect voltage value

Note: The power consumption during power-start to output being stable (release operation) is $2 \mu A$ greater than it is after that period (completion of release operation) because of delay circuit through current.

Release Voltage: VDR = VDF + VHYS
* Transient Delay Time: 1ms to 50ms & 80ms to 400ms versions are also available.

■ OPERATIONAL EXPLANATION

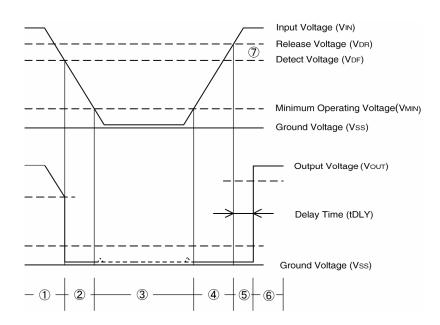
●CMOS output

- ① When a voltage higher than the release voltage (VDR) is applied to the voltage input pin (VIN), the voltage will gradually fall. When a voltage higher than the detect voltage (VDF) is applied to VIN, output (VOUT) will be equal to the input at VIN.
 - Note that high impedance exists at Vout with the N-channel open drain configuration. If the pin is pulled up, Vout will be equal to the pull up voltage.
- ② When VIN falls below VDF, VOUT will be equal to the ground voltage (Vss) level (detect state). Note that this also applies to N-channel open drain configurations.
- When VIN falls to a level below that of the minimum operating voltage (VMIN) output will become unstable. Because the output pin is generally pulled up with N-channel open drain configurations, output will be equal to pull up voltage.
- 4 When VIN rises above the VSS level (excepting levels lower than minimum operating voltage), VOUT will be equal to VSS until VIN reaches the VDR level.
- S Although VIN will rise to a level higher than VDR, VOUT maintains ground voltage level via the delay circuit.
- ⑥ Following transient delay time, VIN will be output at Vout. Note that high impedance exists with the N-channel open drain configuration and that voltage will be dependent on pull up.

Notes:

- 1. The difference between VDR and VDF represents the hysteresis range.
- 2. Propagation delay time (tDLY) represents the time it takes for VIN to appear at VouT once the said voltage has exceeded the VDR level.

Timing Chart



■DIRECTIONS FOR USE

Notes on Use

- 1. Please use this IC within the stated maximum ratings. The IC is liable to malfunction should the ratings be exceeded.
- 2. When a resistor is connected between the VIN pin and the input with CMOS output configurations, oscillation may occur as a result of voltage drops at RIN if load current (IOUT) exists. It is therefore recommend that no resistor be added. (refer to Oscillation Description (1) below)
- 3. When a resistor is connected between the Vin pin and the input with CMOS output configurations, irrespective of N-ch output configurations, oscillation may occur as a result of through current at the time of voltage release even if load current (Iout) does not exist. (refer to Oscillation Description (2) below)
- 4. With a resistor connected between the VIN pin and the input, detect and release voltage will rise as a result of the IC's supply current flowing through the VIN pin.
- 5. If a resistor (RIN) must be used, then please use with as small a level of input impedance as possible in order to control the occurrences of oscillation as described above.
 - Further, please ensure that RIN is less than $10k\Omega$ and that CIN is more than $0.1\,\mu$ F (Figure 1). In such cases, detect and release voltages will rise due to voltage drops at RIN brought about by the IC's supply current.

Oscillation Description

(1) Oscillation as a result of output current with the CMOS output configuration:

When the voltage applied at IN rises, release operations commence and the detector's output voltage increases. Load current (IOUT) will flow through RL. Because a voltage drop (RIN x IOUT) is produced at the RIN resistor, located between the input (IN) and the VIN pin, the load current will flow via the IC's VIN pin. The voltage drop will also lead to a fall in the voltage level at the VIN pin. When the VIN pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at RIN will disappear, the voltage level at the VIN pin will rise and release operations will begin over again.

Oscillation may occur with this " release - detect - release " repetition.

Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current:

Since the XC61F series are CMOS ICs, through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, oscillation is liable to occur during release voltage operations as a result of output current which is influenced by this through current (Figure 3).

Since hysteresis exists during detect operations, oscillation is unlikely to occur.

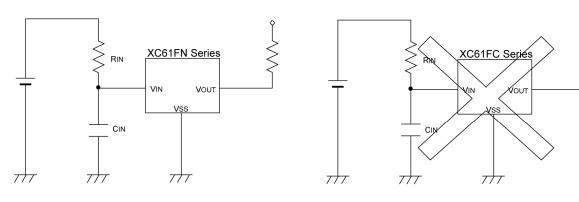


Figure 1. When using an input resistor

■ DIRECTIONS FOR USE (Continued)

Oscillation Description (Continued)

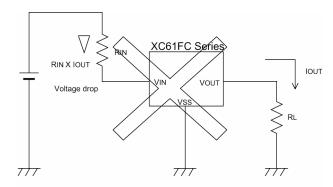


Figure 2. Oscillation in relation to output current

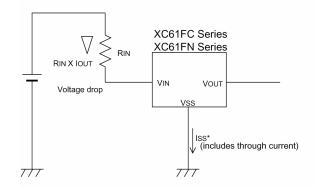


Figure 3. Oscillation in relation to through current

25°C

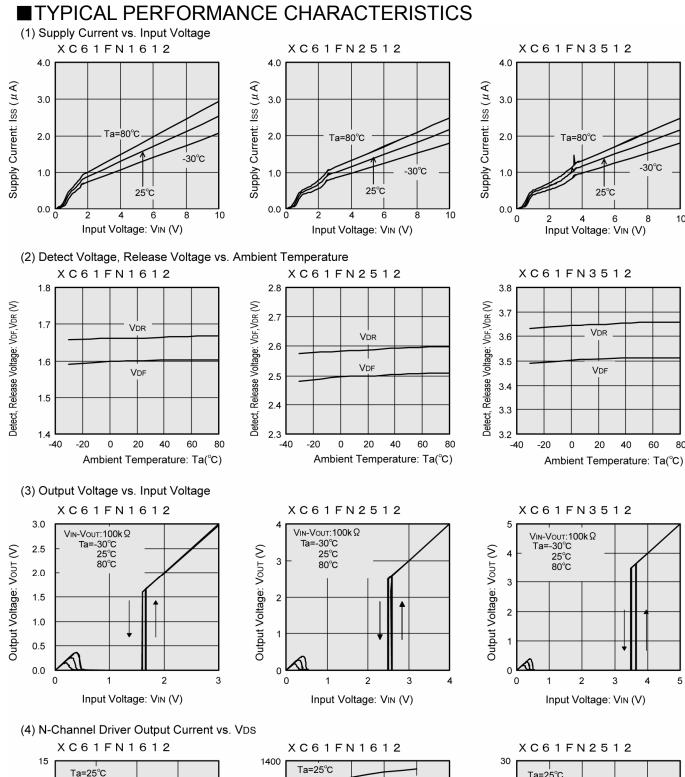
VDR

VDF

20 40

3

60



Ontput Current: Iour (# A)

0

0

0.2

0.4

V_Ds (V)

VIN=1.5V

1.5

2.0

1.0V

1.0

V_Ds (V)

0.5

Output Current: IouT (mA)

12

9

0.0

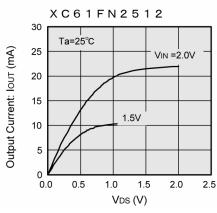
VIN =0.8V

8.0

1.0

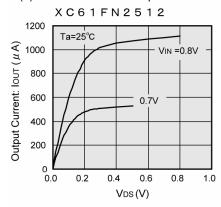
0.7V

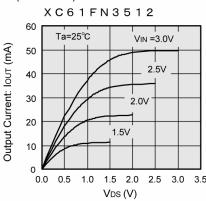
0.6

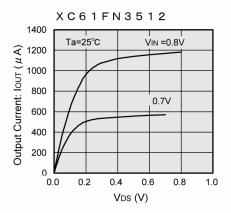


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

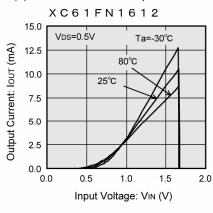
(4) N-Channel Driver Output Current vs. VDS (Continued)

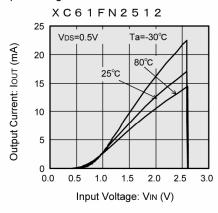


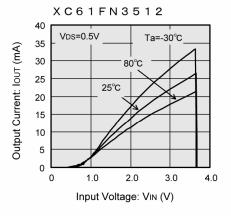




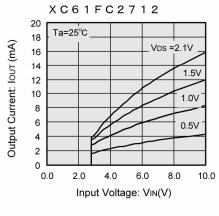
(5) N-Channel Driver Output Current vs. Input Voltage

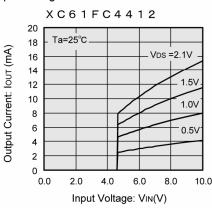




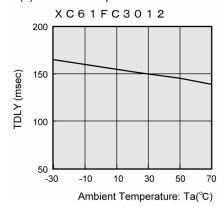


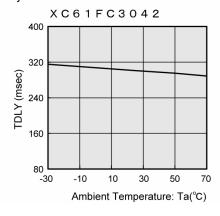
(6) P-Channel Driver Output Current vs. Input Voltage

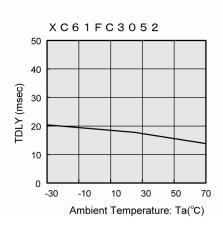




(7) Ambient Temperature vs. Transient Delay Time

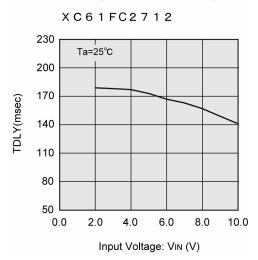






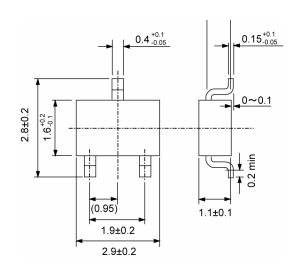
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(8) Input Voltage vs. Transient Delay Time

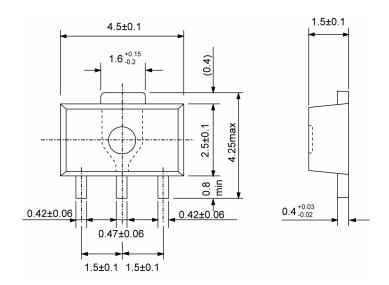


■ PACKAGING INFORMATION

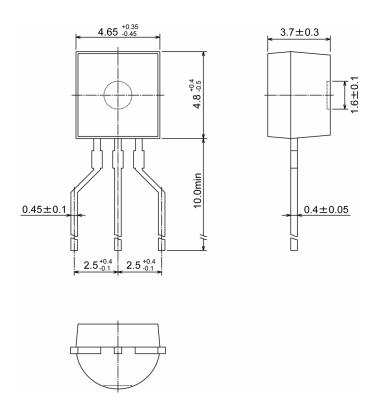
●SOT-23



●SOT-89

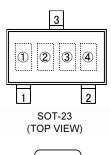


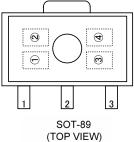
●TO-92



■MARKING RULE

●SOT-23, SOT-89





①Represents integer of detect voltage and output configuration CMOS output (XC61FC series)

MARK	CONFIGURATION	VOLTAGE (V)
Α	CMOS	0.x
В	CMOS	1.x
С	CMOS	2.x
D	CMOS	3.x
E	CMOS	4.x
F	CMOS	5.x
Н	CMOS	6.x

N-channel open drain (XC61FN series)

MARK	CONFIGURATION	VOLTAGE (V)
K	N-ch	0.x
L	N-ch	1.x
M	N-ch	2.x
N	N-ch	3.x
Р	N-ch	4.x
R	N-ch	5.x
S	N-ch	6.x

2) Represents decimal number of detect voltage

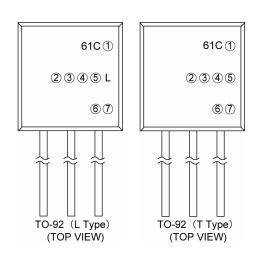
er toprocome decimal number of detect rendge				
MARK	VOLTAGE (V)	MARK	VOLTAGE (V)	
0	x.0	5	x.5	
1	x.1	6	x.6	
2	x.2	7	x.7	
3	x.3	8	x.8	
4	x.4	9	x.9	

3 Represents delay time

VOLTAGE (V)	DELAY TIME
5	50 ~ 200ms
6	80 ~ 400ms
7	1 ~ 50ms

④Represents assembly lot number (Based on internal standards)

●TO-92



①Represents output configuration

MARK	OUTPUT CONFIGURATION
С	CMOS
N	N-ch

2, 3Represents detect voltage

MA	VOLTAGE (V)	
2	3	VOLIAGE (V)
3	3	3.3
5	0	5.0

4 Represents delay time

MARK	DELAY TIME
1	50ms ~ 200ms
4	80ms ~ 400ms
5	1ms ~ 50ms

⑤Represents detect voltage accuracy

MARK	DETECT VOLTAGE ACCURACY
2	Within <u>+</u> 2%

⑥Represents a least significant digit of the production year (ex.)

MARK	PRODUCTION YEAR
3	2003
4	2004

TRepresents production lot number

0 to 9, A to Z repeated (G, I, J, O, Q, W expected)

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